A spin dephasing mechanism mediated by the interplay between the spin-orbit coupling and the asymmetrical confining potential in semiconductor quantum dot

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Understanding the spin dephasing mechanism is of fundamental importance in all potential applications of the spin qubit. Here we demonstrate a spin dephasing mechanism in semiconductor quantum dot due to the 1/f charge noise. The spin-charge interaction is mediated by the interplay between the spin-orbit coupling and the asymmetrical quantum dot confining potential. The dephasing rate is proportional to both the strength of the spin-orbit coupling and the degree of the asymmetry of the confining potential. The evaluated spin dephasing time is about $T_2^\ast = 7 \mu s$, 275 $\mu$s, and 55 ms in a InSb, InAs, and GaAs nanowire quantum dots with a moderate well-height $V_0 = 10$ meV. In particular, the spin dephasing can be enhanced by lowering the well-height. When the well-height is as small as $V_0 = 5$ meV, the spin dephasing time in InSb, InAs, and GaAs quantum dots is reduced to $T_2^\ast = 0.38 \mu s$, 18 $\mu$s, and 9 ms.

I. INTRODUCTION

It is the phase coherence property that differs the quantum bit (qubit) from the classical bit in information processing, such that a quantum computer potentially can solve certain problems more efficiently than a classical computer \cite{1,2}. One prerequisite of building a reliable quantum computer requires that, the building blocks, i.e., the qubits, must have long enough dephasing time \cite{3}. However, for a realistic experimental qubit candidate such as charge qubit \cite{4,5}, spin qubit \cite{6–8}, and Josephson qubit \cite{9–11}, the qubit dephasing time is usually severely limited by unexpected and unavoidable environmental noises. Therefore, understanding various dephasing mechanisms is of practical importance to the implementations of quantum computing.

The quantum dot spin qubit has many merits such as the long coherence time \cite{12,13}, the electrical controllability \cite{14–22}, and the convenience for scalability \cite{23–25}, so that it is most likely to realize quantum computing in semiconductor quantum dot. Fluctuating charge field with 1/f spectrum distribution has been observed in many quantum nano-systems \cite{26–28}. It also limits the phase coherence time of many qubit candidates \cite{9–11,29–31}. As recently observed in experiments \cite{32,33}, the slanting magnetic field in Si quantum dot mediated a spin-charge interaction, which gives rise to the spin pure dephasing. We are motivated to think about whether the spin-orbit coupling (SOC) \cite{34}, internally presented in InSb, InAs, and GaAs quantum dots due to the space-inversion asymmetry, would also mediate a spin dephasing mechanism caused by the 1/f charge noise?

Quantum dot spin dephasing caused by the charge defects via the combined effects of the SOC and the Coulomb interaction is studied in Ref. 35. While the complete quantum theory of the SOC mediated spin dephasing is not well established. Here, let us give a heuristic discussion on how the spin dephasing arises in a simple model of the nanowire quantum dot. The Hamiltonian reads \cite{36–41}

\[ H = \frac{p^2}{2m} + \alpha \sigma^z p + \Delta \sigma^x + V(x), \]

where $m$ is the effective electron mass, $\alpha$ is the Rashba SOC strength \cite{34}, $\Delta = g_{\mu_B} B/2$ is half of the Zeeman splitting, and $V(x)$ is the confining potential. A spin-orbit qubit \cite{19–21} is the encoded to the lowest two energy levels $\Psi_{e,g}(x)$ of the quantum dot. The qubit couples to the fluctuating charge field $E$ via the electric-dipole interaction $eE_x x$ \cite{42}. Hence, the necessary condition of the qubit phase noise is $\langle \Psi_{e|x} | \Psi_{e} \rangle \neq \langle \Psi_{g|x} | \Psi_{g} \rangle$. However, if the confining potential is symmetrical $V(x) = V(-x)$, the model (1) has a $Z_2$ symmetry $[\sigma^z \mathcal{P}, H] = 0$ \cite{43–45}, where $\mathcal{P}$ is the parity. The $Z_2$ symmetry directly leads to $\langle \Psi_{e(x)} | \Psi_{e(x)} \rangle = 0$. Therefore, the phase noise of the qubit can arise only when $V(x)$ is an asymmetrical potential.

In this paper, we formulate a theory of the SOC mediated spin dephasing based on an exactly solvable model of the nanowire quantum dot. We demonstrate that the interplay between the SOC and the asymmetrical confining potential mediates a spin-charge interaction, that gives rise to the spin dephasing in semiconductor quantum dot. Both the SOC and the asymmetry of the confining potential are indispensable in this dephasing mechanism. The larger of the SOC in the quantum dot material, the stronger of the spin dephasing. Likewise, the larger of the degree of the asymmetry of the confining potential, the stronger of the spin dephasing. In quantum dot modeled by a half infinite square well with a moderate well-height $V_0 = 10$ meV, the dephasing time is about $T_2^\ast = 7 \mu s$, 275 $\mu$s, and 55 ms in the InSb, the InAs, and the GaAs materials. When the well-height is chosen as small as $V_0 = 5$ meV, the spin dephasing time is decreased to $T_2^\ast = 0.38 \mu s$, 18 $\mu$s, and 9 ms.

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\[ V(x) = \begin{cases} \infty, & x < 0, \\ 0, & 0 < x < a, \\ V_0, & a < x, \end{cases} \tag{2} \]

where \( V_0 \) and \( a \) are the height and the width of the well, respectively. The confining potential has such a regular shape that the bound states in the well are expected to be exactly solvable [45, 48-50]. The lowest two energy levels in the quantum dot are used to encode a qubit. In the presence of the nontrivial Rashba SOC, the spin operator in Hamiltonian (1) is no longer a good quantum number, such that the qubit defined in our model is actually a spin-orbit qubit [19-21]. In our following considerations, the quantum states span the qubit Hilbert space are marked by the pseudo spin states: \( \Psi_\epsilon(x) \equiv |\uparrow\rangle \) and \( \Psi_\sigma(x) \equiv |\downarrow\rangle \). In contrast to the pure spin qubit, the spin-orbit qubit has the merit of being electrically manipulable [14-21].

The boundary condition is used to determine the energy spectrum and the corresponding eigenfunctions of a quantum system. For the square well (2) we are considering, the boundary condition explicitly reads [45]

\[ \Psi(0) = 0, \Psi(a+0) = \Psi(a-0), \Psi'(a+0) = \Psi'(a-0), \tag{3} \]

where \( \Psi(x) \) is the eigenfunction and \( \Psi'(x) \) is its first derivative. It should be noted that the eigenfunction \( \Psi(x) = [\Psi_1(x), \Psi_2(x)]^T \) has two components due to the spin degree of freedom. Hence, the boundary condition (3) actually contains six independent sub-equations.

Let us say a few words on the model we are considering. First, although our model is very simple, we believe that this model captures the main physics of the SOC mediated spin dephasing in an asymmetrical quantum dot. Second, we expect that the physics (at least qualitatively) in a more realistic 2D quantum dot model would be similar to that in our exactly solvable 1D model. Third, as far as we know, there is no exact solution for a 2D quantum dot with both asymmetrical confining potential and non trivial SOC. Therefore, investigating a simple exactly solvable quantum dot model no doubt gives the first step for understanding the relevant properties in a more complicated and more realistic quantum dot.

In this paper, we mainly study three quantum dot materials, i.e., the InSb, the InAs, and the GaAs, all of which are of current research interest. The InSb has the largest SOC, the InAs has a relative large SOC, and the GaAs has the smallest SOC. In our following calculations, unless otherwise stated, all the parameters are taken from Table I.

### II. THE MODEL

Here we are interested in a 1D model of the nanowire quantum dot with both asymmetrical confining potential and nontrivial Rashba SOC. The explicit Hamiltonian under consideration is given by Eq. (1), and the asymmetrical confining potential is modeled by the following half infinite square well [see Fig. 1(a)]

\[
\frac{\alpha}{2m_0^*} (x/a)^2 + \frac{V_0}{m_0^*} \left( \frac{x}{a} \right) \quad \text{(a)}
\]

The solutions of these transcendental equations give us the total energy spectrum of the quantum dot. Once the spectrum is obtained, the corresponding eigenfunctions are also known. A typical probability density distribution of the ground state in a quantum system. For the square well (2) we are considering, the boundary condition explicitly reads [45]

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### III. THE QUBIT HILBERT SPACE STRUCTURE

We first solve the dispersion relations and the wave functions for the bulk Hamiltonian \( H_b = \frac{p^2}{2m} + \alpha \sigma^z p + \Delta \sigma^x \) [45, 50]. Then the eigenfunction of Hamiltonian (1) can be written as a linear combination of all the degenerate bulk wave functions [48-50]. Inside the well, the eigenfunction can be expanded using both the bulk plane-wave solutions and the bulk exponential-function solutions. Outside the well, the eigenfunction can be expanded using either the bulk combined plane-wave and exponential-function solutions or the bulk exponential-function solutions. Imposing the boundary condition (3) on the expanded eigenfunction, we obtain a series of transcendental equations with respect to the energy region [see appendices A, B, and C]. The solutions of these transcendental equations give us the total energy spectrum of the quantum dot. Once the spectrum is obtained, the corresponding eigenfunctions are also known. A typical probability density distribution of the ground state in a quantum system. For the square well (2) we are considering, the boundary condition explicitly reads [45]

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from the figures, with the decease of the well-height $V_0$, the energies of the quantum states become smaller, i.e., more close to the portal of the well, and the qubit level splitting becomes smaller too. This phenomena has been observed previously, the spin-orbit effect in quantum dot can be enhanced by lowering the height of the confining potential [45]. It should be noted that, the well-height $V_0$ in our model can not be arbitrary small if we want at least two bound states presented in the well.

In Figs. 2(d)-(f), we also show the lowest two energy levels as a function of the well-width $a$. There are no obvious changes for the qubit level splitting when the well-width $a$ is varied in our considered region. However, with the decrease of the well-width $a$, the energies of the corresponding quantum states becomes larger, i.e., more closer to the portal of the well. Likewise, the well-width $a$ also can not be arbitrary small if we want to maintain at least two bound states in the well.

The spin-orbit qubit can couple to the charge noise via the electric-dipole interaction $eE_xx$ [42], where $E_xx$ is the $x$ component of the fluctuating charge field. Hence, we need to determine the form of the electric-dipole operator $x$ in the qubit Hilbert space. The phase noise of the qubit arises when the average values of $x$ between the first excited state $x_e \equiv \langle \Psi_e | x | \Psi_e \rangle$ and the ground state $x_g \equiv \langle \Psi_g | x | \Psi_g \rangle$ are different. Since the exact eigenfunctions in the quantum dot are already obtained [see e.g., Fig. 1(b)], these two quantities $x_e$ and $x_g$ are easy to evaluate.

In Figs. 3(a)-(c), we show the difference of the averages $x_e - x_g$ as a function of the well-height $V_0$ in the InSb, the InAs, and the GaAs quantum dots, respectively. In consistence with the $V_0$ dependence of the energy spectrum, here with the decrease of the well height $V_0$, the difference of the averages $x_e - x_g$ becomes larger, i.e., the spin-orbit effect becomes stronger. In Figs. 3(d)-(f), we also show the difference of the averages $x_e - x_g$ as a function of the well-width $a$. For materials with both strong SOC and relative small effective electron mass such as InSb and InAs, with the decrease of the well-width $a$, the difference $x_e - x_g$ becomes larger. While for the material with weak SOC and relative large effective electron mass, e.g., GaAs, with the decrease of the well-width $a$, the difference $x_e - x_g$ becomes smaller instead. Actually, if we continue to reduce the GaAs quantum dot size $a$ to smaller value such as 30 nm, after a critical value $a_c$, the difference $x_e - x_g$ also increases with the decrease of $a$ until the two bound states are repelled out of the well.

IV. THE SPIN PURE DEPHASING

In III-V semiconductor quantum dot, the spin dephasing mechanism caused by the surrounding magnetic noise is well established [51-53]. It is the magnetic dipole interactions between the lattice nuclear spins produces a fluctuating hyperfine field felt by the electron spin. $1/f$ charge noise universally exists in many quantum nano-
structures [26–28], and it has also been observed in more and more quantum dot experiments [33, 54–56], hence it is desirable to examine whether the charge noise would give rise to spin dephasing in spin-orbit coupled quantum dots. In particular, in a recent experiment performed on a InSb nanowire quantum dot, the experiment can not rule out the spin dephasing mechanism induced by the $1/f$ charge noise [57].

The spin-orbit qubit in the semiconductor quantum dot can couple to the charge field via the electric-dipole interaction. The total Hamiltonian describing the qubit-noise interaction reads

$$H_{\text{tot}} = H + e \cos \theta \sum_k \Xi_k (b_k + b_k^\dagger) + \sum_k \hbar \omega_k b_k^\dagger b_k,$$

where we have written the fluctuating charge field as $E = \sum_k \Xi_k \tilde{e}_k (b_k + b_k^\dagger)$ [42], with $\Xi_k$ being the charge field in the wavevector space and $\tilde{e}_k$ being the direction of the charge field, and $\theta$ is the angle between $\tilde{e}_k$ and the axis of the nanowire $\vec{x}$. In our following calculations, we have averaged over all possible angle $\theta$ for the obtained physical quantities, e.g., $\langle \Gamma(t) \rangle_\theta = \int_0^{2\pi} \Gamma(t) d\theta / 2\pi$.

When we focus only on the qubit Hilbert subspace, the total Hamiltonian can be reduced to (only phase noise is taken into account)

$$H_{\text{tot}} = \frac{E_e - E_g}{2} \langle \hat{\psi}_+ \hat{\psi}_- - |\psi_+ \rangle \langle \psi_- | \rangle + \sum_k \hbar \omega_k b_k^\dagger b_k$$

$$+ \sum_k \langle \hat{x}_e | \hat{\psi}_+ \rangle \langle \hat{\psi}_+ | \hat{x}_g \rangle \langle \hat{\psi}_- | \hat{x}_g \rangle \hbar \Xi_k \cos \theta \langle b_k + b_k^\dagger \rangle,$$

where $E_e, g$ are the energies of the first excited state $|\Psi_e(x) \rangle \equiv | \psi_+ \rangle$ and the ground state $|\Psi_g(x) \rangle \equiv | \psi_- \rangle$, respectively. Obviously, if $x_e = x_g$, the spin-orbit qubit can not couple to the charge noise. From this viewpoint, it is the difference of the average values of the electric-dipole operator $x_e - x_g$, which originates from the interplay between the SOC and the asymmetrical confining potential, gives rise to the pure dephasing of the spin-orbit qubit in semiconductor quantum dot.

The model we derived is very similar to the spin-boson model [58–60]. A simple analysis shows that the dephasing of this model is also exactly solvable, the decay rate can be written as

$$\Gamma_{\text{ph}}(t) = \frac{(x_e - x_g)^2}{2a^2} \int_{\omega_{\text{min}}}^{\omega_{\text{max}}} d\omega S(\omega) \sin^2(\omega t / 2)/(\omega / 2)^2,$$

where the spectrum function is defined as

$$S(\omega) = \sum_k \frac{e^2 \Xi_k^2 a^2 k_B T \hbar^3}{\hbar^3 \omega} \delta(\omega - \omega_k) = \frac{A_{\omega, a, T}^2}{\omega},$$

where $A_{\omega, a, T}^2 = \langle \hat{x}_e | \hat{\psi}_+ \rangle \langle \hat{\psi}_+ | \hat{x}_g \rangle \langle \hat{\psi}_- | \hat{x}_g \rangle \hbar \Xi_k \cos \theta \langle b_k + b_k^\dagger \rangle$.

![FIG. 5. The dephasing time $T_2^*$ as a function of the well height $V_0$. (a) In the InSb quantum dot. (b) In the InAs quantum dot. (c) In the GaAs quantum dot.](image)

![FIG. 6. The dephasing time $T_2^*$ as a function of the well width $a$. (a) In the InSb quantum dot. (b) In the InAs quantum dot. (c) In the GaAs quantum dot.](image)
In Fig. 6, we show the qubit dephasing time $T_\ast^2$ as a function of the quantum dot size $a$. As can be seen from the figure, in InSb and InAs quantum dots, because the qubit energy levels are shallow energy levels in the well, i.e., close to the portal of the well $V_0$ [see Figs. 2(d) and (e)], reducing the quantum dot size $a$ leads to a shorter dephasing time $T_\ast^2$ [see Figs. 6(a) and (b)]. However, in GaAs quantum dot, the qubit energy levels are very deep energy levels in the well, i.e., far away from the portal of the well $V_0$ [see Fig. 2(f)], reducing the quantum dot size $a$ leads to a longer dephasing time $T_\ast^2$ [see Fig. 6(c)].

Note that when the qubit energy levels in the GaAs quantum dot become shallow energy levels, e.g., by tuning the quantum dot size to smaller value such as $a = 30$ nm, the above discussion is no longer applicable.

V. SUMMARY

In summary, in this paper we built a theory of the spin dephasing due to the $1/f$ charge noise in a spin-orbit coupled semiconductor quantum dot. We have investigated a simple exactly solvable 1D quantum dot with both Rashba SOC and asymmetrical confining potential. Using analytical method, we obtain exactly the energy spectrum and the corresponding eigenfunctions in the quantum dot. The average values of the electric-dipole operator in the ground and the first excited states are different, such that the qubit phase noise due to the $1/f$ charge noise arises naturally in our model. It should be noted that the difference of electric-dipole operator originates from the interplay between the SOC and the asymmetrical confining potential of the semiconductor quantum dot.

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Appendix A: The transcendental equations in the strong SOC regime: $\Delta < ma^2$

The eigenfunction of Hamiltonian (1) can be written as a linear combination of all the degenerate bulk wave functions, where the bulk Hamiltonian reads $H_b = \frac{p^2}{2m} + a\sigma^z p + \Delta \sigma^x$. There are three types of bulk dispersion relations, i.e., the plane-wave solution [50] [see Fig. 7(a)]

$$E_{b}^\pm = \frac{k^2}{2m} \pm \sqrt{\alpha^2 k^2 + \Delta^2}, \quad (A1)$$

the exponential-function solution [50] [see Fig. 7(b)]

$$E_{b}^\pm = -\frac{\Gamma^2}{2m} \pm \sqrt{-\alpha^2 \Gamma^2 + \Delta^2}, \quad (A2)$$

and the combined plane-wave and exponential-function solution [45] [see Fig. 7(c)]

$$\frac{E_{b}^\pm}{ma^2} = -1 \pm \sqrt{(1 - \frac{\Delta^2}{m^3 \alpha^4 \sin^2 2\phi} \cos^2 2\phi)} \frac{\cos \theta_1^* \sin \theta_2^* \cos \theta_2}{\sin^2 2\phi}. \quad (A3)$$

In the classical allowed region $0 < x < a$, the eigenfunction should be expanded using the plane-wave solutions and the exponential-function solutions, and we can divide the energy region into four sub-regions. While in the classical forbidden region $a < x$, the eigenfunction must be expanded using the combined plane-wave and exponential-function solutions.

1. In the energy region: $-\frac{1}{2}ma^2 - \frac{\Delta^2}{2m} < E < -\Delta$

In this energy region, inside the well $0 < x < a$, the eigenfunction can be written as [50]

$$\Psi(x) = c_1 \left( \sin \frac{\theta_1}{2} - \cos \frac{\theta_1}{2} \right) e^{ik_1 x} + c_2 \left( \cos \frac{\theta_1}{2} - \sin \frac{\theta_1}{2} \right) e^{-ik_1 x} + c_3 \left( \sin \frac{\theta_2}{2} - \cos \frac{\theta_2}{2} \right) e^{ik_2 x} + c_4 \left( \cos \frac{\theta_2}{2} - \sin \frac{\theta_2}{2} \right) e^{-ik_2 x}, \quad (A4)$$
where \( \theta_{1,2} = \arctan[\Delta/(\alpha k_{1,2})] \), and \( k_{1,2} \) is a function of the quantum dot energy \( E \) to be determined

\[
k_{1,2} = \sqrt{2ma} \sqrt{1 + \frac{E}{m^2a^2} + \frac{\Delta^2}{m^2a^4}}.
\]  

(A5)

Outside the well \( a < x \), the eigenfunction can be written as [45]

\[
\Psi(x) = c_5 \left( \frac{1}{Re^{i\Phi}} \right) e^{ik_\rho x \cos \phi - k_\rho x \sin \phi} + c_6 \left( \frac{Re^{-i\Phi}}{1} \right) e^{-ik_\rho x \cos \phi - k_\rho x \sin \phi},
\]

(A6)

where

\[
R \cos \Phi = -\frac{ma^2 + \alpha k_\rho \cos \phi}{\Delta},
\]

\[
R \sin \Phi = -\frac{k_\rho \sin 2\phi + 2ma k_\rho \sin \phi}{2ma}.
\]

(A7)

and

\[
k_\rho \cos \phi = k_x = ma \sqrt{1 + \frac{E - V_0}{m^2a^2} + \sqrt{\frac{(E - V_0)^2 - \Delta^2}{m^2a^4}}},
\]

\[
k_\rho \sin \phi = k_y = ma \sqrt{1 - \frac{E - V_0}{m^2a^2} + \sqrt{\frac{(E - V_0)^2 - \Delta^2}{m^2a^4}}},
\]

(A8)

We have six coefficients \( c_{i=1,\ldots,6} \) to be determined. The boundary condition (3) happens to have six sub-equations, such that the boundary condition can be formally written as a matrix equation \( \mathbf{M} \cdot \mathbf{C} = 0 \), where the matrix \( \mathbf{M} \) reads

\[
\mathbf{M} = \begin{pmatrix}
\sin \frac{\theta_1}{2} & \cos \frac{\theta_1}{2} & \sin \frac{\theta_2}{2} & \cos \frac{\theta_2}{2} & 0 & 0 \\
\cos \frac{\theta_1}{2} & -\sin \frac{\theta_1}{2} & \cos \frac{\theta_2}{2} & -\sin \frac{\theta_2}{2} & 0 & 0 \\
e^{ik_1a} \sin \frac{\theta_1}{2} & e^{-ik_1a} \cos \frac{\theta_1}{2} & e^{ik_2a} \sin \frac{\theta_2}{2} & e^{-ik_2a} \cos \frac{\theta_2}{2} & e^{-ik_\rho a - k_y a} & e^{ik_\rho a - k_y a} \\
-e^{ik_1a} \cos \frac{\theta_1}{2} & e^{-ik_1a} \sin \frac{\theta_1}{2} & -e^{ik_2a} \cos \frac{\theta_2}{2} & e^{-ik_2a} \sin \frac{\theta_2}{2} & -R e^{ik_\rho a - k_y a + \Phi} & e^{-ik_\rho a - k_y a} \\
-ik_1 e^{ik_1a} \sin \frac{\theta_1}{2} & -ik_1 e^{-ik_1a} \cos \frac{\theta_1}{2} & -ik_2 e^{ik_2a} \sin \frac{\theta_2}{2} & -ik_2 e^{-ik_2a} \cos \frac{\theta_2}{2} & -(ik_x - k_y) & (ik_x + k_y) R \\
-ik_1 e^{-ik_1a} \cos \frac{\theta_1}{2} & ik_1 e^{ik_1a} \sin \frac{\theta_1}{2} & ik_2 e^{ik_2a} \sin \frac{\theta_2}{2} & ik_2 e^{-ik_2a} \cos \frac{\theta_2}{2} & -(ik_x - k_y) R & (ik_x + k_y) \times e^{ik_\rho a - k_y a + \Phi} \\
& & & & \times e^{-ik_\rho a - k_y a - \Phi} & \\
& & & & \times e^{-ik_\rho a - k_y a - \Phi} & \\
& & & & \times e^{-ik_\rho a - k_y a - \Phi} & \\
& & & & \times e^{-ik_\rho a - k_y a - \Phi} & \\
& & & & \times e^{-ik_\rho a - k_y a - \Phi} &
\end{pmatrix}.
\]

(A9)

The condition that there exists nontrivial solution for the matrix equation directly gives rise to

\[
\det (\mathbf{M}) = 0.
\]

(A10)

This equation is an implicit equation of the energy \( E \), the solution of which gives us the energy spectrum of the quantum dot in the priorly announced energy region.
2. In the energy region: \(-\Delta < E < -\frac{\hbar^2}{2m^*}\)

In this energy region, inside the well \(0 < x < a\), the eigenfunction can be written as [50]

\[
\Psi(x) = c_1 e^{-i\varphi x} \left( \frac{-e^{-i\varphi}}{1} \right) + c_2 e^{i\Gamma x} \left( \frac{e^{-i\varphi}}{1} \right) + c_3 e^{ikx} \left( \frac{\sin \frac{\theta}{2}}{-\cos \frac{\theta}{2}} \right) + c_4 e^{-ikx} \left( \frac{\cos \frac{\theta}{2}}{-\sin \frac{\theta}{2}} \right),
\]

where \(\theta = \arctan[\Delta/(\alpha k)]\), \(\varphi = \arctan(\alpha \Gamma/\sqrt{-\alpha^2 \Gamma^2 + \Delta^2})\), and \(k\) and \(\Gamma\) are a function of the quantum dot energy \(E\) to be determined

\[
k = \sqrt{2m\alpha} \sqrt{1 + \frac{E}{m\alpha^2}} + \sqrt{1 + \frac{2E}{m\alpha^2} + \frac{\Delta^2}{m^2\alpha^4}},
\]

\[
\Gamma = \sqrt{2m\alpha} \sqrt{1 - \frac{E}{m\alpha^2} + \sqrt{1 + \frac{2E}{m\alpha^2} + \frac{\Delta^2}{m^2\alpha^4}}},
\]

Outside of the well \(a < x\), the eigenfunction can still be written as the form given in Eq. (A6). In this case the matrix \(M\) reads

\[
M = \begin{pmatrix}
-e^{-i\varphi} & -e^{i\varphi} & \sin \frac{\theta}{2} & \cos \frac{\theta}{2} & 0 & 0 \\
1 & 1 & -\cos \frac{\theta}{2} & -\sin \frac{\theta}{2} & -e^{ika} a - k_x a & -R \\
-e^{-\Gamma a - i\varphi} & -e^{\Gamma a + i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-i\varphi} & e^{i\varphi} & -e^{ika} \sin \frac{\theta}{2} & -e^{-ika} \cos \frac{\theta}{2} & -e^{ika} a - k_x a & -R \\
e^{-\Gamma a - i\varphi} & -e^{\Gamma a + i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a - i\varphi} & -e^{\Gamma a + i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a - i\varphi} & -e^{\Gamma a + i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a - i\varphi} & -e^{\Gamma a + i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0
\end{pmatrix}.
\]

3. In the energy region: \(-\frac{\hbar^2}{2m^*} < E < \Delta\)

In this energy region, inside the well \(0 < x < a\), the eigenfunction can be written as [50]

\[
\Psi(x) = c_1 e^{-\Gamma x} \left( \frac{e^{i\varphi}}{1} \right) + c_2 e^{\Gamma x} \left( \frac{e^{-i\varphi}}{1} \right) + c_3 e^{ikx} \left( \frac{\sin \frac{\theta}{2}}{-\cos \frac{\theta}{2}} \right) + c_4 e^{-ikx} \left( \frac{\cos \frac{\theta}{2}}{-\sin \frac{\theta}{2}} \right).
\]

Outside of the well \(a < x\), the eigenfunction can still be written as the form given in Eq. (A6). In this case the matrix \(M\) reads

\[
M = \begin{pmatrix}
e^{i\varphi} & e^{-i\varphi} & \sin \frac{\theta}{2} & \cos \frac{\theta}{2} & 0 & 0 \\
1 & 1 & -\cos \frac{\theta}{2} & -\sin \frac{\theta}{2} & -e^{ika} a - k_x a & -R \\
e^{-\Gamma a + i\varphi} & e^{\Gamma a - i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-i\varphi} & e^{i\varphi} & -e^{ika} \sin \frac{\theta}{2} & -e^{-ika} \cos \frac{\theta}{2} & -e^{ika} a - k_x a & -R \\
e^{-\Gamma a + i\varphi} & e^{\Gamma a - i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a + i\varphi} & e^{\Gamma a - i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a + i\varphi} & e^{\Gamma a - i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & 0 & 0
\end{pmatrix}.
\]

4. In the energy region: \(\Delta < E\)

In this energy region, inside the well \(0 < x < a\), the eigenfunction can be written as [50]

\[
\Psi(x) = c_1 \left( \frac{\cos \frac{\theta_1}{2}}{\sin \frac{\theta_1}{2}} \right) e^{ik_1 x} + c_2 \left( \frac{\sin \frac{\theta_1}{2}}{\cos \frac{\theta_1}{2}} \right) e^{-ik_1 x} + c_3 \left( \frac{\sin \frac{\theta_2}{2}}{-\cos \frac{\theta_2}{2}} \right) e^{ik_2 x} + c_4 \left( \frac{\cos \frac{\theta_2}{2}}{-\sin \frac{\theta_2}{2}} \right) e^{-ik_2 x}.
\]
Outside of the well $a < x$, the eigenfunction can still be written as the form given in Eq. (A6). In this case the matrix $M$ reads

$$M = egin{pmatrix}
\cos \frac{\theta_1}{2} & \sin \frac{\theta_1}{2} & 0 & 0 \\
\sin \frac{\theta_1}{2} & \cos \frac{\theta_1}{2} & 0 & 0 \\
e^{i k_1 a} \cos \frac{\theta_1}{2} & e^{-i k_1 a} \sin \frac{\theta_1}{2} & -e^{-i k_2 a} \cos \frac{\theta_2}{2} & -e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
-e^{i k_1 a} \sin \frac{\theta_1}{2} & -e^{-i k_1 a} \cos \frac{\theta_1}{2} & e^{-i k_2 a} \cos \frac{\theta_2}{2} & e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
e^{i k_1 a} \sin \frac{\theta_1}{2} & -e^{-i k_1 a} \cos \frac{\theta_1}{2} & -e^{-i k_2 a} \cos \frac{\theta_2}{2} & -e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
e^{i k_1 a} \cos \frac{\theta_1}{2} & e^{-i k_1 a} \sin \frac{\theta_1}{2} & e^{-i k_2 a} \cos \frac{\theta_2}{2} & e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
e^{i k_1 a} \sin \frac{\theta_1}{2} & -e^{-i k_1 a} \cos \frac{\theta_1}{2} & -e^{-i k_2 a} \cos \frac{\theta_2}{2} & -e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
e^{-i k_1 a} \sin \frac{\theta_1}{2} & e^{i k_1 a} \cos \frac{\theta_1}{2} & e^{-i k_2 a} \cos \frac{\theta_2}{2} & e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
e^{-i k_1 a} \cos \frac{\theta_1}{2} & -e^{i k_1 a} \sin \frac{\theta_1}{2} & e^{-i k_2 a} \cos \frac{\theta_2}{2} & e^{-i k_2 a} \sin \frac{\theta_2}{2} \\
\end{pmatrix}$$

(A17)

**Appendix B: The transcendental equations in the intermediate SOC regime: $\frac{\Delta}{2} < m\alpha^2 < \Delta$**

In the intermediate SOC regime, the bulk dispersion relations are shown in Fig. 8. In the classical allowed region $x < a$, the energy region is divide into three sub-regions. While in the classical forbidden region $a < x$, the energy region is divided into two sub-regions.

1. **In the energy region**: $-\Delta < E < -\frac{\Delta^2}{2m\alpha^2}$ \( \cap \) \( E - V_0 < -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2 \)

In this case the Matrix $M$ is the same as that given in Eq. (A13).

2. **In the energy region**: $-\Delta < E < -\frac{\Delta^2}{2m\alpha^2}$ \( \cap \) \( -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2 < E - V_0 < -\Delta \)

In this energy region, inside the well $0 < x < a$, the eigenfunction is still written as the form given in Eq. (A11). Outside the well $a < x$, the eigenfunction reads

$$\Psi(x) = c_5 e^{-\Gamma_1 x} \left( -e^{-i\varphi_1} \frac{1}{1} \right) + c_6 e^{-\Gamma_2 x} \left( -e^{-i\varphi_2} \frac{1}{1} \right),$$

(B1)

where $\varphi_{1,2} = \arctan(\alpha \Gamma_{1,2}/\sqrt{-\alpha^2 \Gamma_{1,2}^2 + \Delta^2})$, and $\Gamma_{1,2}$ are a function of the quantum dot energy $E$ to be determined

$$\Gamma_{1,2} = \sqrt{2m\alpha} \sqrt{-1 - \frac{E - V_0}{m\alpha^2} + \sqrt{1 + \frac{2(E - V_0)}{m\alpha^2} + \frac{\Delta^2}{m^2\alpha^4}}},$$

(B2)
In this case the matrix $M$ reads

$$
M = \begin{pmatrix}
-e^{-i\varphi} & -e^{i\varphi} & \sin \frac{\theta}{2} & \cos \frac{\theta}{2} & 0 & 0 \\
1 & 1 & -\cos \frac{\theta}{2} & -\sin \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a-i\varphi} & e^{-\Gamma a+i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & e^{-\Gamma a-i\varphi_1} & e^{-\Gamma a+i\varphi_2} \\
e^{-\Gamma a-i\varphi} & e^{\Gamma a+i\varphi} & -e^{ika} \cos \frac{\theta}{2} & -e^{-ika} \sin \frac{\theta}{2} & e^{-\Gamma a+i\varphi_1} & -e^{-\Gamma a-i\varphi_2} \\
\Gamma e^{-\Gamma a-i\varphi} & -\Gamma e^{\Gamma a+i\varphi} & -ike^{ika} \sin \frac{\theta}{2} & ike^{-ika} \cos \frac{\theta}{2} & -\Gamma_1 e^{-\Gamma a-i\varphi_1} & -\Gamma_2 e^{-\Gamma a+i\varphi_2} \\
-\Gamma e^{-\Gamma a-i\varphi} & \Gamma e^{\Gamma a+i\varphi} & -ike^{-ika} \cos \frac{\theta}{2} & ike^{ika} \sin \frac{\theta}{2} & \Gamma_1 e^{-\Gamma a+i\varphi_1} & \Gamma_2 e^{-\Gamma a-i\varphi_2}
\end{pmatrix}.
$$  \tag{B3}

3. In the energy region: $-\frac{\Delta^2}{2m\alpha^2} < E < \Delta \cap E-V_0 < -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2$

In this case the matrix $M$ is the same as that given in Eq. (A15).

4. In the energy region: $-\frac{\Delta^2}{2m\alpha^2} < E < \Delta \cap -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2 < E < V_0 < -\Delta$

In this energy region, inside the well $0 < x < a$, the eigenfunction is written as the form given in Eq. (A14). Outside the well $a < x$, the eigenfunction is written as the form given in Eq. (B1). In this case the matrix $M$ reads

$$
M = \begin{pmatrix}
e^{i\varphi} & e^{-i\varphi} & \sin \frac{\theta}{2} & \cos \frac{\theta}{2} & 0 & 0 \\
1 & 1 & -\cos \frac{\theta}{2} & -\sin \frac{\theta}{2} & 0 & 0 \\
e^{-\Gamma a+i\varphi} & e^{\Gamma a-i\varphi} & e^{ika} \sin \frac{\theta}{2} & e^{-ika} \cos \frac{\theta}{2} & e^{-\Gamma a+i\varphi_1} & e^{-\Gamma a-i\varphi_2} \\
e^{-\Gamma a-i\varphi} & e^{\Gamma a+i\varphi} & -e^{ika} \cos \frac{\theta}{2} & -e^{-ika} \sin \frac{\theta}{2} & e^{-\Gamma a+i\varphi_1} & -e^{-\Gamma a-i\varphi_2} \\
\Gamma e^{-\Gamma a+i\varphi} & -\Gamma e^{\Gamma a+i\varphi} & -ike^{ika} \sin \frac{\theta}{2} & ike^{-ika} \cos \frac{\theta}{2} & -\Gamma_1 e^{-\Gamma a+i\varphi_1} & -\Gamma_2 e^{-\Gamma a-i\varphi_2} \\
-\Gamma e^{-\Gamma a-i\varphi} & \Gamma e^{\Gamma a+i\varphi} & -ike^{-ika} \cos \frac{\theta}{2} & ike^{ika} \sin \frac{\theta}{2} & \Gamma_1 e^{-\Gamma a+i\varphi_1} & \Gamma_2 e^{-\Gamma a-i\varphi_2}
\end{pmatrix}.
$$  \tag{B4}

5. In the energy region: $\Delta < E \cap E-V_0 < -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2$

In this case the matrix $M$ is the same as that given in Eq. (A17).

6. In the energy region: $\Delta < E \cap -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2 < E < V_0 < -\Delta$

In this energy region, inside the well $0 < x < a$, the eigenfunction is written as the form given in Eq. (A16). Outside the well $a < x$, the eigenfunction is written as the form given in Eq. (B1). In this case the matrix $M$ reads

$$
M = \begin{pmatrix}
\cos \frac{\theta_1}{2} & \sin \frac{\theta_1}{2} & \sin \frac{\theta_2}{2} & \cos \frac{\theta_2}{2} & 0 & 0 \\
\sin \frac{\theta_1}{2} & \cos \frac{\theta_1}{2} & -\cos \frac{\theta_2}{2} & -\sin \frac{\theta_2}{2} & 0 & 0 \\
e^{ik_1 a} \cos \frac{\theta_1}{2} & e^{-ik_2 a} \sin \frac{\theta_1}{2} & e^{ik_1 a} \sin \frac{\theta_1}{2} & e^{ik_2 a} \cos \frac{\theta_1}{2} & e^{-\Gamma a-i\varphi_1} & e^{-\Gamma a+i\varphi_2} \\
e^{-ik_1 a} \cos \frac{\theta_1}{2} & -e^{-ik_2 a} \sin \frac{\theta_1}{2} & -e^{ik_1 a} \sin \frac{\theta_1}{2} & -e^{ik_2 a} \cos \frac{\theta_1}{2} & -e^{-\Gamma a+i\varphi_1} & -e^{-\Gamma a-i\varphi_2} \\
ike^{ik_1 a} \cos \frac{\theta_1}{2} & -ike^{ik_2 a} \sin \frac{\theta_1}{2} & ike^{-ik_1 a} \sin \frac{\theta_1}{2} & ike^{ik_2 a} \cos \frac{\theta_1}{2} & -\Gamma_1 e^{-\Gamma a-i\varphi_1} & -\Gamma_2 e^{-\Gamma a+i\varphi_2} \\
ike^{-ik_1 a} \sin \frac{\theta_1}{2} & -ike^{-ik_2 a} \cos \frac{\theta_1}{2} & -ike^{ik_1 a} \cos \frac{\theta_1}{2} & ike^{-ik_2 a} \sin \frac{\theta_1}{2} & \Gamma_1 e^{-\Gamma a+i\varphi_1} & \Gamma_2 e^{-\Gamma a-i\varphi_2}
\end{pmatrix}.
$$  \tag{B5}

Appendix C: The transcendental equations in the weak SOC regime: $m\alpha^2 < \frac{\Delta}{2}$

In the weak SOC regime, the bulk dispersion relations are shown in Fig. 9. In the classical allowed region $x < a$, the energy region is divide into two sub-regions. While in the classical forbidden region $a < x$, the energy region is divided into three sub-regions.

1. In the energy region: $-\Delta < E < \Delta \cap E-V_0 < -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2} m\alpha^2$

In this case the matrix $M$ is the same as that given in Eq. (A15).
2. In the energy region: \(-\Delta < E < \Delta \cap -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2}m\alpha^2 < E - V_0 < -\frac{\Delta^2}{2m\alpha^2}\)

In this case the Matrix \(M\) is the same as that given in Eq. (B4).

3. In the energy region: \(-\Delta < E < \Delta \cap -\frac{\Delta^2}{2m\alpha^2} < E - V_0 < -\Delta\)

In this energy region, inside the well \(0 < x < a\), the eigenfunction is written as the form given in Eq. (A14). Outside the well \(a < x\), the eigenfunction reads

\[
\Psi(x) = c_5 e^{-\Gamma_1 x} \begin{pmatrix} e^{i\phi_1} \\ 1 \end{pmatrix} + c_6 e^{-\Gamma_2 x} \begin{pmatrix} -e^{-i\phi_2} \\ 1 \end{pmatrix},
\]

(C1)

In this case the matrix \(M\) reads

\[
M = \begin{pmatrix} e^{i\phi} & e^{-i\phi} & \sin \theta & \cos \theta & 0 & 0 \\ e^{-\Gamma_1 a + i\phi} & e^{\Gamma_1 a - i\phi} & -\cos \theta & -\sin \theta & 0 & 0 \\ e^{-\Gamma_2 a + i\phi} & e^{\Gamma_2 a - i\phi} & -e^{-i\kappa a} & e^{i\kappa a} & -e^{-\Gamma_1 a + i\phi_1} & e^{-\Gamma_2 a - i\phi_2} \\ -\Gamma e^{-\Gamma_1 a + i\phi} & \Gamma e^{\Gamma_1 a - i\phi} & k e^{i\kappa a} & -k e^{-i\kappa a} & -e^{-\Gamma_1 a} & e^{\Gamma_2 a} \\ -\Gamma e^{-\Gamma_2 a + i\phi} & \Gamma e^{\Gamma_2 a - i\phi} & -k e^{i\kappa a} & k e^{-i\kappa a} & -e^{-\Gamma_1 a + i\phi_1} & e^{\Gamma_2 a} \\ -\Gamma e^{-\Gamma_1 a} & \Gamma e^{\Gamma_1 a} & -k e^{i\kappa a} & k e^{-i\kappa a} & \Gamma_1 e^{-\Gamma_1 a} & \Gamma_2 e^{\Gamma_2 a} \end{pmatrix}.
\]

(C2)

4. In the energy region: \(\Delta < E \cap E - V_0 < -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2}m\alpha^2\)

In this case the Matrix \(M\) is the same as that given in Eq. (A17).

5. In the energy region: \(\Delta < E \cap -\frac{\Delta^2}{2m\alpha^2} - \frac{1}{2}m\alpha^2 < E - V_0 < -\frac{\Delta^2}{2m\alpha^2}\)

In this case the Matrix \(M\) is the same as that given in Eq. (B5).
6. In the energy region: $\Delta < E < 0$ and $-\frac{\hbar^2}{2m_e} < E < -\Delta$

In this energy region, inside the well $0 < x < a$, the eigenfunction is written as the form given in Eq. (A16). Outside the well $a < x$, the eigenfunction is written as the form given in Eq. (C1). In this case the matrix $M$ reads

$$M = \begin{pmatrix}
\cos \frac{\theta_1}{2} & \sin \frac{\theta_1}{2} & \sin \frac{\theta_2}{2} & \cos \frac{\theta_2}{2} & 0 & 0 \\
\sin \frac{\theta_1}{2} & \cos \frac{\theta_1}{2} & -\cos \frac{\theta_2}{2} & \sin \frac{\theta_2}{2} & 0 & 0 \\
e^{i k_1 a} \cos \frac{\theta_1}{2} & e^{-i k_1 a} \sin \frac{\theta_1}{2} & e^{i k_2 a} \cos \frac{\theta_2}{2} & e^{-i k_2 a} \sin \frac{\theta_2}{2} & e^{-\Gamma_1 a + i \varphi_1} & e^{-\Gamma_1 a - i \varphi_2} \\
e^{i k_1 a} \sin \frac{\theta_1}{2} & e^{-i k_1 a} \cos \frac{\theta_1}{2} & -e^{i k_2 a} \sin \frac{\theta_2}{2} & -e^{-i k_2 a} \cos \frac{\theta_2}{2} & -e^{-\Gamma_1 a + i \varphi_1} & -e^{-\Gamma_1 a - i \varphi_2} \\
\Gamma_1 e^{i \Gamma_1 a + \gamma_1} & \Gamma_1 e^{-i \Gamma_1 a} & \Gamma_2 e^{i \Gamma_2 a} & \Gamma_2 e^{-i \Gamma_2 a} & 0 & 0 \\
\end{pmatrix}. \ (C3)$$

[50] R. Li, Phys. Rev. B 97, 085430 (2018);